1. Scope :

This specification applies to PIN silicon photodiode chips,
Device No. PD-0131

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy .

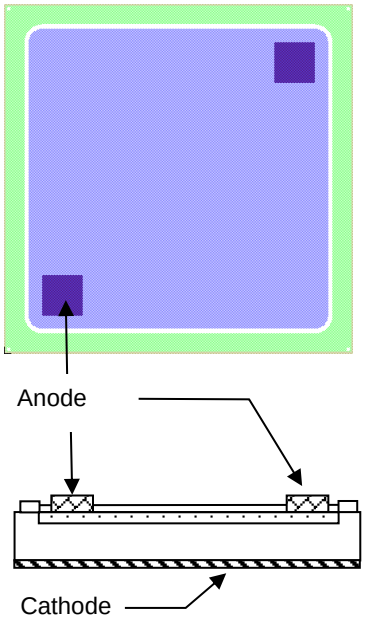
3. Size :

3-1. Chip size : 132.0 mils x 132.0 mils (3.353 mm x 3.353 mm).
3-2. Chip thickness : 12.0 ± 1.5 mils (0.305 ± 0.038 mm).
3-3. Active area : 113.0 mils x 113.0 mils (2.870 mm x 2.870 mm).
3-4. Bonding pad (Anode) : 15.0 mils x 15.0 mils (0.381 mm x 0.381 mm).
3-5. Pattern drawing : Refer to the attached drawing.

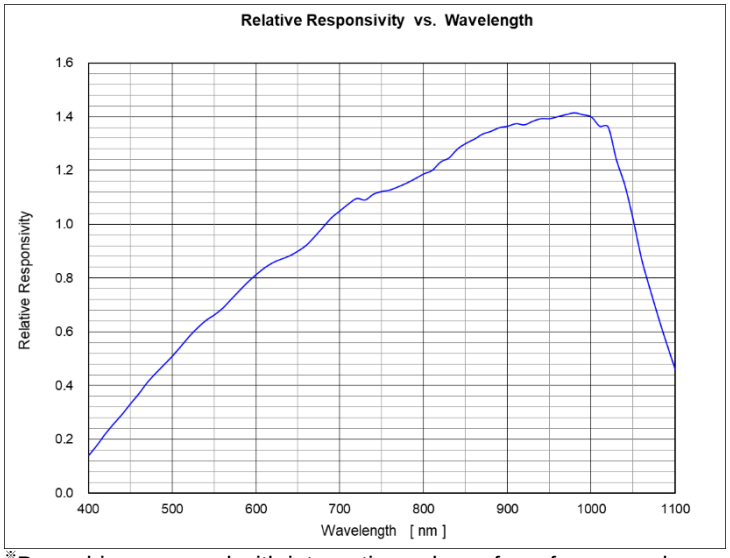
4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D	V_R=10V Ee=0mW/cm²			30	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee=0mW/cm²	60			V
Open circuit Voltage	Voc	T=2856K Ee=5mW/cm²		350		mV
Short circuit Current	Isc	T=2856K Ee=5mW/cm²		83		μA
Reverse light Current	I_L	V_R =5V T=2856K Ee=5mW/cm²		85		μA
Total Capacitance	C_t	V_R =5V Ee=0mW/cm² f=1MHz		19		pF

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.